Package

SSSMini3-F1

Code

2SJ0674

Silicon P-channel MOS FET

For switching circuits

■ Features

- Low ON resistance Ron
- High-speed switching
- SSSMini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

■ Absolute Maximum Ratings $T_a = 25$ °C

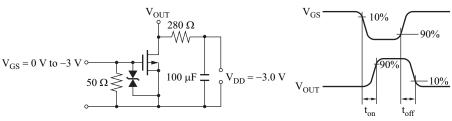
V
T 7
V
mA
mA
nW
°C
°C

■ Electrical Characteristics $T_a = 25$ °C±3°C

 High-speed switching 			SSS	Mini3-F1					
• SSSMini type package, allowing do	_	of the equipn	nent and Pin	Name					
automatic insertion through the tape packing 1: G						-6	∞ .		
			2: 8	ource		XO	9		
■ Absolute Maximum Ratings T _a =	= 25°C		3: [Drain	•				
Parameter	Symbol	Rating	Unit	Marking Symbols Ell					
Drain-source surrender voltage	V _{DSS}	-30 V Walking Symbol: 50							
Gate-source surrender voltage	V_{GSS}	±12	SSSMini3-F1 Pin Name 1: Gate 2: Source 3: Drain Marking Symbol: 5U V MA MA MM MW 125 °C						
Drain current	I_D	-100	mA	Auc					
Peak drain current	I_{DP}	-200	mA						
Power dissipation	P _D	100	mW						
Channel temperature	T _{ch}	125	°C 400	j j			:0°		
Storage temperature	T _{stg}	-55 to +125	°C CO K/6			~			
* • • •			WII CO	6		de.			
■ Electrical Characteristics $T_a = 25$	5°C±3°C		and the	1706	•.4	HO.			
Parameter	Symbo	1	Conditions	Min	Тур	Max	Unit		
Drain-source surrender voltage	V _{DSS}	$I_D = -10 \mu$	A, V ₆₈ = 0	3 0	XO C	0	V		
Drain-source cutoff current	I _{DSS}	$V_{DS} = -20$	$VV_{GS} = 0$	01/1/		-1.0	μΑ		
Gate-source cutoff current	I _{GSS}	$V_{GS} = \pm 10$	$V_{,V_{DS}}=0$		VI2	±10	μΑ		
Gate threshold voltage	V	I _D − 1.0 μ	$A_{\rm N}V_{\rm DS} = -3.0 \rm V$	-0.5	-1.0	-1.5	V		
Drain-source ON resistance	D		$A, V_{GS} = -2.5 V$	TILL	13	30	Ω		
Diani-source ON resistance	R _{DS(on)}	$I_{\rm D} = -10 \text{pr}$	$I_D = -10 \text{ mA}, V_{GS} = -4.0 \text{ V}$		9	18			
Forward transfer admittance	Y _{fs}	$I_D = -10 \text{ m}$	$_{DA}$, $V_{DS} = -3$ V , $f = 1$ kHz	20	40		mS		
Short-circuit input capacitance	C _{iss}		110, 116		12		pF		
(Common source)	Ciss		in for the		12	þi			
Short-circuit output capacitance	Coss	$V_{DS} = -3$	$V_{\rm GS} = 0, f = 1 \text{ MHz}$		13		рF		
(Common source)	033	_ 0	, ds ,						
Reverse transfer capacitance	C _{rss}	33			7		pF		
(Common source)					200				
Turn-on time *	t _{on}		$V_{GS} = 0 \text{ V to } -3 \text{ V}, I_D = -10 \text{ mA}$		300		ns		
Turn-off time *	t _{off}	$V_{DD} = -3 V$	$V_{GS} = -3 \text{ V to } 0 \text{ V}, I_D = -10 \text{ mA}$		400		ns		

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

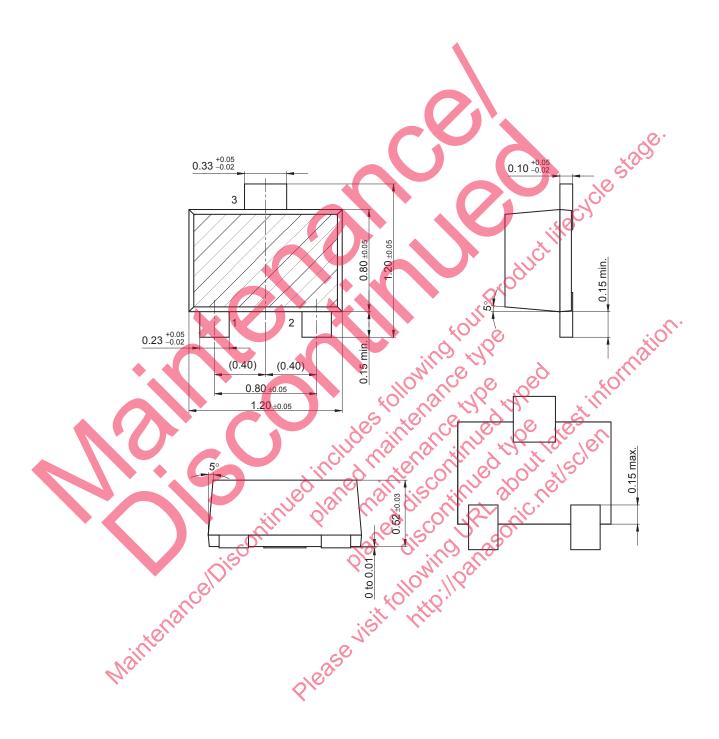
2. * : t_{on} , t_{off} measurement circuit



2SJ0674 Panasonic

SSSMini3-F1

Unit: mm



Request for your special attention and precautions in using the technical information and semiconductors described in this book

- (1) If any of the products or technical information described in this book is to be exported or provided to non-residents, the laws and regulations of the exporting country, especially, those with regard to security export control, must be observed.
- (2) The technical information described in this book is intended only to show the main characteristics and application circuit examples of the products, and no license is granted under any intellectual property right or other right owned by our company or any other company. Therefore, no responsibility is assumed by our company as to the infringement upon any such right owned by any other company which may arise as a result of the use of technical information described in this book.
- (3) The products described in this book are intended to be used for standard applications or general electronic equipment (such as office equipment, communications equipment, measuring instruments and household appliances). Consult our sales staff in advance for information on the following applications:
 - · Special applications (such as for airplanes, aerospace, automobiles, traffic control equipment, combustion equipment, life support systems and safety devices) in which exceptional quality and reliability are required, or if the failure or malfunction of the products may directly jeopardize life or harm the human body.
 - · Any applications other than the standard applications intended.
- (4) The products and product specifications described in this book are subject to change without notice for modification and/or improvement. At the final stage of your design, purchasing, or use of the products, therefore, ask for the most up-to-date Product Standards in advance to make sure that the latest specifications satisfy your requirements.
- (5) When designing your equipment, comply with the range of absolute maximum rating and the guaranteed operating conditions (operating power supply voltage and operating environment etc.). Especially, please be careful not to exceed the range of absolute maximum rating on the transient state, such as power-on, power-off and mode-switching. Otherwise, we will not be liable for any defect which may arise later in your equipment.
- Even when the products are used within the guaranteed values, take into the consideration of incidence of break down and failure mode, possible to occur to semiconductor products. Measures on the systems such as redundant design, arresting the spread of fire or preventing glitch are recommended in order to prevent physical injury, fire, social damages, for example, by using the products.
- (6) Comply with the instructions for use in order to prevent breakdown and characteristics change due to external factors (ESD, EOS) thermal stress and mechanical stress) at the time of handling, mounting or at customer's process. When using products for which damp-proof packing is required, satisfy the conditions, such as shelf life and the clapsed time since first opening the packages.
- (7) This book may be not reprinted or reproduced whether wholly or partially, without the prior written permission of Matsushita Please visit following har acroin nation with the please visit following har acroin nation with planed discontinued Electric Industrial Co., Ltd. Maintenance Discontinued includ

OHOMING UKL BOOUT 18 ESTE